

Triple Well Flash Memory and Fabrication Process

ABSTRACT OF THE DISCLOSURE

A structure for a flash memory cell is described in which a triple well is formed with the memory cell residing in a P-well, which in turn is deposited in an N-well in a P-type substrate. The structure provides the ability to operate such memories with considerably lower operating potentials than prior art devices. A process for fabricating the flash memory cell is also described.

Figs. 2A and 2B